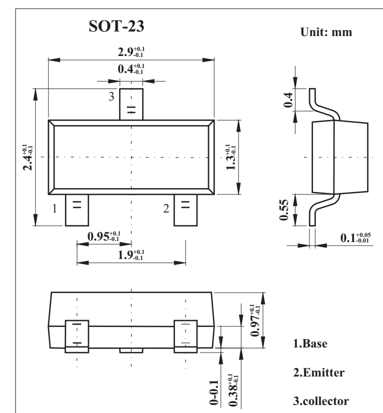
NPN Epitaxial Planar Silicon Transistor

2SC3689



Features

- Small Cob (Cob=1.5pF typ).
- Adoption of FBET process.
- High DC current gain (h_{FE}=800 to 3200).
- Low collector-to-emitter saturation voltage ($V_{CE(sat)}$≤0.5V).
- High V_{EBO} (V_{EBO}≥15V).

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	15	V
Collector current	I_C	100	mA
Collector current (pulse)	I_{cp}	200	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	125	℃
Storage temperature	T_{stg}	-55 to +125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	V_{CB} = 40V, I_E=0			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB} = 10V, I_C=0			0.1	μA
DC current gain	h_{FE}	V_{CE} =5V , I_C = 10mA	800	1500	3200	
Gain bandwidth product	f_T	V_{CE} = 10V , I_C = 10mA		200		MHz
Output capacitance	C_{ob}	V_{CB} = 10V , f = 1.0MHz		1.5		pF
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C = 50mA , I_B = 1mA		0.1	0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C = 50mA , I_B = 1mA		0.8	1.1	V
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C = 10μA , I_E = 0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C = 1mA , R_{BE} = ∞	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E = 10μA , I_C = 0	15			V

Marking

Marking	GY